#3

PTO/SB/08A

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known	
Application Number	10/073,506
Filing Date	February 11, 2002
Confirmation Number	6190
First Named Inventor	Robert J. Falster
Group Art Unit	1775
Examiner Name	
Attorney Docket No.	MEMC 98-1451/2554.1

Sheet | of 10

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document: Number	U.S. Patent Document: Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
	1	4,314,885		Yamamoto et al.	02/1982
	2	4,376,657		Nagasawa et al.	03/1983
	3	4,437,922		Bischoff et al.	03/1984
	4	4,505,759		O'Mara	03/1985
	5	4,548,664		Tobin	10/1985
	6	4,851,358		Huber	07/1989
	7	4,868,133		Huber	09/1989
	8	4,981,549		Yamashita et al.	01/1991
	9	5,264,189		Yamashita et al.	11/1993
	10	5,327,007		Imura et al.	07/1994
	11	5,401,669		Falster et al.	03/1995
	12	5,403,406		Falster et al.	04/1995
	13	5,445,975		Gardner et al.	08/1995
	14	5,474,020		Bell et al.	12/1995
	15	5,485,803		Habu	01/1996

Examiner Signature		Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

#3

OIPE MAY 16 2002 PATENT & TRADEMARK OFFICE

PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/073,506
				Filing Date	February 11, 2002
(use as many sheets as necessary)				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	2	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

RECEIVED MAY 21 2002 TC 1700

	16	5,487,354		von Ammon et al.	01/1996
	17	5,502,010		Nadahara et al.	03/1996
	18	5,502,331		Inoue et al.	03/1996
	19	5,534,294		Kubota et al.	07/1996
	20	5,539,245		Imura et al.	07/1996
	21	5,593,494		Falster	01/1997
	22	5,611,855		Wijaranakula	03/1997
	23	5,667,584		Takano et al.	09/1997
	24	5,674,756		Satoh et al.	10/1997
	25	5,704,973		Sakurada et al.	01/1998
	26	5,728,211		Takano et al.	03/1998
	27	5,738,942		Kubota et al.	04/1998
	28	5,788,763		Hayashi et al.	08/1998
	29	5,919,302		Falster et al.	07/06/1999
	30	5,935,320		Graef et al.	08/10/1999
	31	5,939,770		Kageyama	08/1999
	32	5,942,032		Kim et al.	08/24/1999
	33	5,944,889		Park et al.	08/1999
	34	5,954,873		Hourai et al.	09/1999
	35	5,968,262		Saishouji et al.	10/1999

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

#3

OIPE MAY 16 2002 PATENT & TRADEMARK OFFICE

RECEIVED MAY 21 2002 TC 1700

PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/073,506
				Filing Date	February 11, 2002
(use as many sheets as necessary)				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	3	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

	36	5,968,264		Lida et al.	10/1999
	37	6,045,610		Park et al.	04/2000
	38	6,053,974		Luter et al.	04/25/2000
	39	6,093,913		Schrenker et al.	07/25/2000
	40	6,153,008		von Ammon et al.	11/28/2000
MM	41	6,190,631	B1	Falster	02/20/2001
	42	6,228,164		von Ammon et al.	05/08/2001
MM	43	6,254,672	B1	Falster et al.	07/03/2001
MM	44	6,287,380	B1	Falster et al.	09/11/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Office	Foreign Patent Document: Number[4]	Foreign Patent Document: Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T[6]
	45	EP	0 504 837	A2		09/1992	
	46	EP	0 503 816	B1		09/1992	
	47	EP	0 536 958	A1		04/1993	
	48	EP	0 716 168	A1		06/1996	
	49	EP	0 747 513	A2	Shin-Estu Handotai Company Ltd.	12/11/1996	
	50	EP	0 799 913	A1		10/1997	

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

PTO/SB/08A	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/073,506
	Filing Date	February 11, 2002
(use as many sheets as necessary)	Confirmation Number	6190
	First Named Inventor	Robert J. Falster
	Group Art Unit	1775
	Examiner Name	
Sheet 4 of 10	Attorney Docket No.	MEMC 98-1451/2554.1

	51	EP	0 890 662		Shinetsu Handotai KK	01/13/1999	
	52	EP	0 909 840		Shinetsu Handotai KK	04/21/1999	
	53	EP	0 962 557	A1	Shin-Etsu Handotai Company Ltd.	05/21/1999	
	54	EP	0 962 556	A1		08/1999	
	55	DE	39 05 626	A1		08/1989	
	56	DE	43 23 964	A1		01/1994	
	57	DE	44 14 947	A1		08/1995	
	58	DE	198 06 045	A1		08/1998	
	59	JP	2-180789			07/1990	
	60	JP	Hei 3-93700		Nippon Steel Corp.	04/18/1991	
	61	JP	4-108682			04/1992	
MA	62	JP	Hei 7-041383		Nippon Steel Corp.et al.	02/10/1995	
MA	63	JP	Hei 7-206591		Nippon Steel Corp.et al.	08/08/1995	
	64	JP	7321120 (Abstract Only)			12/1995	
	65	JP	7335657 (Abstract Only)			12/1995	
	66	JP	8045947 (Abstract Only)			02/1996	
	67	JP	8045944 (Abstract Only)			02/1996	
	68	JP	8-045945			02/1996	

Examiner Signature	Matthew Andrews	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

PTO/SB/08A	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/073,506
	Filing Date	February 11, 2002
(use as many sheets as necessary)	Confirmation Number	6190
	First Named Inventor	Robert J. Falster
	Group Art Unit	1775
	Examiner Name	
Sheet 5 of 10	Attorney Docket No.	MEMC 98-1451/2554.1

MM	69	JP	Hei 8-208374		Nippon Steel Corp. et al	08/13/1996	
	~~70~~	~~JP~~	~~HO 8-268794~~		~~Sumitomo Sitix Corp.~~	~~10/15/1996~~	
	~~71~~	~~JP~~	8-330316 (Pub. Hei 07-158458)		Sumitomo Sitix Corp.	12/1996	
	~~72~~	~~JP~~	~~9-199416~~			~~07/1997~~	
	~~73~~	~~JP~~	~~9-202690~~			~~08/1997~~	
	~~74~~	~~JP~~	~~11-150119~~	~~A~~		~~06/1999~~	
	~~75~~	~~JP~~	~~11-157995~~	~~A~~		~~06/1999~~	
	~~76~~	~~JP~~	~~11-180800~~	~~A~~		~~07/1999~~	
	~~77~~	~~JP~~	~~11-189495~~	~~A~~		~~07/1999~~	
	~~78~~	~~JP~~	~~11-199386~~	~~A~~		07/1999	
	~~79~~	~~JP~~	~~11-199387~~	~~A~~		07/1999	
	~~80~~	~~WO~~	~~97/26393~~			~~07/1997~~	
	~~81~~	~~WO~~	~~98/45507~~			~~10/1998~~	
	~~82~~	~~WO~~	~~98/45508~~			~~10/1998~~	
	~~83~~	~~WO~~	~~98/45509~~			~~10/1998~~	
	~~84~~	~~WO~~	98/45510			~~10/1998~~	
	85	GB	2 137 524	~~A~~	~~Hitachi Ltd. (Japan)~~	10/10/1984	
	86	GB	2182 262 A			~~05/1987~~	

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/073,506
				Filing Date	February 11, 2002
(use as many sheets as necessary)				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	6	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
	87	ABE, et al., "Defect-Free Surfaces of Bulk Wafers by Combination of RTA and Crystal Growth", (publication information unknown).	
	88	ABE, et al., "Innovated Silicon Crystal Growth and Wafering Technologies", Electrochemical Society Proceedings, Volume 97, No. 3, pp. 123-133.	
	89	ABE, T., et al., "Behavior of Point Defects in FZ Silicon Crystals", Semiconductor Silicon 1990, *Proceedings of the Sixth International Symposium on Silicon Materials Science and Technology*, Vol. 90-7 (1990), pp. 105-116	
	90	DE KOCK, A.J.R., "The Elimination of Vacancy Cluster Formation in Dislocation -Free Silicon Crystals", J. of the Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, Vol. 118, No. 11, (Nov. 1971), pp.1851-1856	
	91	DE KOCK, A.J.R., et al., "Effect of Growth Parameters on Formation and Elimination of Vacancy Clusters in Dislocation-Free Silicon Crystals", Journal of Crystal Growth, Vol. 22 (1974), pp. 311-320	
MAA	92	DE KOCK, A.J.R., "Point Defect Condensation in Dislocation-Free Silicon Crystals", Semiconductor Silicon, 1977, pp. 508-520.	
	93	DE KOCK, et al., "The Effect of Doping on the Formation of Swirl Defects in Dislocation-Free Czochralski-Grown Silicon crystals", Journal of Crystal Growth, Vol. 49, pp. 718-734 (1980).	
	94	DORNBERGER et al., "The Dependence of Ring Like Distributed Stacking Faults on the Axial Temperature Gradient of Growing Czochralski Silicon Crystals", Electrochemical Society Proceedings, Volume 95-4, pp. 294-305 (1995).	
	95	DORNBERGER, E., et al., "Simulation of Grown-In Voids in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Volume 97, No. 22, pp. 40-49	
	96	DORNBERGER, E., et al., "The Impact of Dwell Time Above 900°C During Crystal Growth on the Gate Oxide Integrity of Silicon Wafers", Electrochemical Society Proceedings, Volume 96, No. 13, pp. 140-151.	

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/073,506
				Filing Date	February 11, 2002
(use as many sheets as necessary)				Confirmation Number	6190
				First Named Inventor	Robert J. Falster
				Group Art Unit	1775
				Examiner Name	
Sheet	7	of	10	Attorney Docket No.	MEMC 98-1451/2554.1

	97	~~DORNBERGER, E., et al., "Simulation of Non-Uniform Grown-In Void Distributions in Czochralski~~ Silicon Crystals", Electrochemical Society Proceedings, Vol. 98, Vol. 1, pp. 490-503	
	98	EIDENZON, A.M., et al., "Influence of growth rate on swirl defects in large dislocation-free crystals of ~~silicon grown by the Czochralski method~~" Soviet Physics Crystallography, Vol. 30(5), (1985), pp. 576-580	
	99	EIDENZON, A.M., et al., "Defect-Free Silicon Crystals Grown by the Czochralski Technique" Inorganic Materials, Vol. 33-3 (1997) pp. 219-225	
	100	~~FOLL, H., et al. "The Formation of Swirl Defects in Silicon by Agglomeration of Self-Interstitials",~~ Journal of Crystal Growth, 1977, pp. 90-1087, Vol. 40, North-Holland Publishing Company	
	101	Hara, et al., "Enhancement of Oxygen Precipitation in Quenched Czochralski Silicon Crystals", J. Appl. Phys., Vol. 66, No. 8, pp. 3958-3960 (1989).	
	102	HOURAI, M., et al., "Improvement of Gate Oxide Integrity Characteristics of CZ-Grown Silicon ~~Crystals", Progress in Semiconductor Fabrication presented by: Semiconductor Equipment and~~ Materials International, Semicon/Europa 93, March 30-April 1, 1993, Geneva, Switzerland	
	103	HOURAI, M., et al. "Growth Parameters ~~Determining the Type of Grown-In Defects in Czockralski~~ Silicon Crystals", Materials Science Forum, Vols. 196-201 (1995) pp. 1713-1718	
	104	~~International Search Report for Application No. PCT/US 99/24068 dated October 13, 1999, 7 pages.~~	
	105	IZUNOME K., et al., "Light Point Defects on Hydrogen Annealed Silicon Wafer, Jpn. J. Appl. Phys. Vol. 36, pp. L1127-L1129, 1997	
	106	JACOB, et al., "Determination of Vacancy Concentrations in the Bulk of Silicon Wafers by Platinum Diffusion Experiments", J. Appl. Phys., Vol. 82, No. 1, pp. 182-191 (1997).	
	107	KISSINGER, et al., "A Method for Studying the Grown-In Defect Density Spectra in Czochralski Silicon Wafers", J. Electrochem. Soc., Vol. 144, No. 4, pp. 1447-1456 (1997).	
	108	LEMKE, H., et al., "Analytical Approximations for the Distributions of Intrinsic Point Defects in Grown Silicon Crystals", Phys. Stat. Sol. (a) Vol. 176 (1999), pp. 843-865	

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

PTO/SB/08A	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	09/416,998
	Filing Date	October 13, 1998
(use as many sheets as necessary)	Confirmation Number	6867
	First Named Inventor	Robert J. Falster et al.
	Group Art Unit	1765
	Examiner Name	
Sheet 8 of 10	Attorney Docket No.	MEMC 98-1451 (2554.1)

	109	MIYAZAKI M., et al., "Microstructure Observation of 'Crystal-Originated Particles' on Silicon Wafers", Jpn. J. Appl. Phys., Vol. 34, pp. 6303-6307, 1995	
	110	NAKAMURA, Koze, et al., "Formation Process of Grown-In Defects in Czochralski Grown Silicon Crystals", Journal of Crystal Growth, Vol. 180, pp. 61-72, 1997.	
MAA	111	PARK, J.G., et al., "Nature of D-Defect in CZ Silicon: D-Defect Dissolution and D-Defect Related T.D.D.B.", Material Science Forum, Vol.s. 196-201, 1995, pp. 1697-1706.	✓
	112	PARK, J.G., et al., "Effect of Crystal Defects on Device Characteristics", *Proceedings of the Symposium on* Crystalline Defects and Contamination: Their Impact And Control In Device Manufacturing II, Proceed. Vol. 97-22 (1997), pp.173-195	
	113	PUZANOV, N.I., et al., "Influence of Transitional Crystallization Regimes on Microdefects in Silicon", USSR Academy of Sciences Newsletter, Vol. 22, No. 8 (1986), pp.1237-1242	X
	114	PUZANOV, N.I.,et al., "Relaxation In A System Of Point Defects In A Growing Dislocation-Free Crystal Of Silicon", Sov. Phys. Crystallogr., Vol. 31, No. 2, (1986) pp. 219-222.	
	115	PUZANOV, N.I., et al., "The effect of thermal history during crystal growth on oxygen precipitation in Czochralski-grown silicon", Semicond. Sci. Technol., Vol. 7, (1992), pp. 406-413	
	116	PUZANOV, N., et al., "Formation of the bands of anomalous oxygen precipitation in Czochralski-grown Si crystals" Journal of Crystal Growth vol. 137, (1994), pp. 642-652	
	117	PUZANOV, N., et al., "The Role of Intrinsic Point Defects in the Formation of Oxygen Precipitation Centers in Dislocation-Free Silicon" Crystallography Reports, Vol. 41, No. 1, (1996), pp. 134-141	
	118	PUZANOV, N.I., et al., "Cultivation, Morphology and Structural Integrity of Dislocation-Free Silicon Tetracrystals", Inorganic Materials, Vol. 32, No. 8 (1996), pp. 903-912	X
	119	PUZANOV, N.L., et al., "Harmful Microdefects in the Seed-End Portion of Large-Diameter Silicon Ingots", Inorganic Materials, Vol. 33, No. 8, (1997) pp. 765-769	
	120	PUZANOV, N., et al., "Modelling microdefect distribution in dislocation-free Si crystals grown from the melt", Journal of Crystal Growth, 178, (1997), pp. 468-478	

Examiner Signature	Matthew Andessa	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	09/416,998
	Filing Date	October 13, 1999
(use as many sheets as necessary)	Confirmation Number	6867
	First Named Inventor	Robert J. Falster et al.
	Group Art Unit	1765
	Examiner Name	
Sheet 9 of 10	Attorney Docket No.	MEMC 98-1451 (2554.1)

	121	PUZANOV, N., et al., "Role of Vacancies in the Nucleation of Ringlike-patterned Oxidation-Induced Stacking Faults in Melt-grown Silicon Crystals" Inorganic Materials, Vol. 34-4, (1998) pp. 307-314	
	122	ROKSNOER, P.J., "Microdefects in a Non-Striated Distribution in Floating-Zone Silicon Crystals", Journal of Crystal Growth, Vol. 53 (1981), pp. 563-573	
	123	ROKSNOER, P.J., "The Mechanism of Formation of Microdefects in Silicon", Journal of Crystal Growth, Vol. 68 (1984), pp. 596-612	
	124	SHIMANUKI, Y., et al., "Effects of Thermal History on Microdefect Formation in Czochralski Silicon Crystals", Japanese Journal of Applied Physics, Vol. 24, No. 12, (1985), pp. 1594-1599	
	125	SINNO, T., et al., "On the Dynamics of the Oxidation-Induced Stacking-Fault Ring in as-grown Czochralski silicon crystals", Applied Physics Letters, Vol. 70, No. 17, pp. 2250-2252, 1997.	
	126	SINNO, T., et al., "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals", J. Electrochem. Soc., Vol. 145, No. 1, pp. 302-318, 1998.	
MM	127	TAKANO, K., et al., "Relationship Between Grown-in Defects and Thermal History During CZ Si Crystal Growth", Materials Science Forum, Vols. 196-201, 1995, pp. 1707-1712.	1
	128	TAN, T. Y., "Point Defects, Diffusion Processes, and Swirl Defect Formation in Silicon", Appl. Phys. A., Vol. 37, pp. 1-17, 1985.	
	129	VANHELLEMONT, J., et al., "Defects in As-Grown Silicon and Their Evolution During Heat Treatments", Materials Science Forum, Vols. 258-263, pp. 341-346, 1997.	
	130	von AMMON et al., "The Dependence of Bulk Defects on the Axial Temperature Gradient of Silicon Crystals During Czochralski Growth", Journal of Crystal Growth, Vol. 151, pp. 273-277 (1995).	
	131	von AMMON et al. "Bulk properties of very large diameter silicon single crystals" Journal of Crystal Growth, Vol. 198/199, (1999), pp. 390-398	
	132	VORONKOV, V., et al., "Behaviour and Effects of Intrinsic Point Defects in the Growth of Large Silicon Crystals", Electrochemical Society Proceedings, Volume 97-22, pp. 3-17 (1997).	
	133	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643 (1982).	

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

#3

PTO/SB/08A **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** (use as many sheets as necessary)				***Complete if Known***	
				Application Number	09/416,998
				Filing Date	October 13, 1999
				Confirmation Number	6867
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	1765
				Examiner Name	
Sheet	10	of	10	Attorney Docket No.	MEMC 98-1451 (2554.1)

	134	WIJARANAKULA, W., "Effect of high-temperature annealing on the dissolution of the *D*-defects in *n*-type Czochralski silicon", Appl. Phys. Lett., Vol. 68, No. 8 , (1994), pp.1030-1032	
	135	WIJARANAKULA, W., "Numerical Modeling of the Point Defect Aggregation during the Czochralski Silicon Crystal Growth", Journal of Electrochemical Society, Vol. 139, No. 2 (Feb. 1992), pp.604-616	
	136	WINKLER, et al., "Improvement of the Gate Oxide Integrity by Modifying Crystal Pulling and Its Impact on Device Failures", J. Electrochem. Soc., Vol. 141, No. 5, pp. 1398-1401 (1994).	
MA	137	YAMAGISHI, et al., "Recognition of D Defects in Silicon Signle Crystals by Preferential Etching and Effect on Gate Oxide Integrity", Semicond. Sci Technol. 7, 1992, A135-A140.	✓
MA	138	YAMAUCHI, et al., "Application of Copper-Decoration Method to Characterize As-Grwon Czochralski-Silicon", Jpn. J. Appl. Phys., Vol. 31, 1992, pp. L439-L442.	✓
	139	ZIMMERMAN, H., et al. "Gold and Platinum Diffusion: the Key to the Understanding of Intrinsic Point Defect Behavior in Silicon", Applied Physics A Solids and Surfaces, Vol. A55, No. 1 (1992) pp. 121-134	
	140	ZIMMERMAN, H., et al. "Vacancy concentration wafer mapping in silicon" Journal of Crystal Growth, Vol. 129, (1993) pp. 582-592.	

Examiner Signature	Matthew Anderson	Date Considered	11/20/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Unique citation designation number. [2]See attached Kinds of U.S. Patent Documents. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.